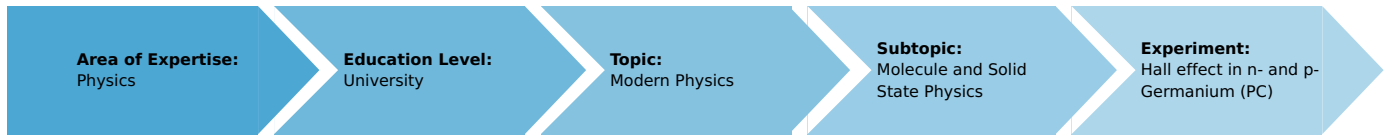


# Hall effect in n- and p-germanium (PC) (Item No.: P2530116)

## Curricular Relevance



### Difficulty



Difficult

### Preparation Time



1 Hour

### Execution Time



2 Hours

### Recommended Group Size



2 Students

### Additional Requirements:

- PC

### Experiment Variations:

### Keywords:

Semiconductor, band theory, forbidden zone, intrinsic conductivity, extrinsic conductivity, valence band, conduction band, Lorentz force, magnetic resistance, mobility, onductivity, band spacing, Hall coefficient

## Overview

## Short description

### Principle

The resistivity and Hall voltage of a rectangular germanium sample are measured as a function of temperature and magnetic field. The band spacing, the specific conductivity, the type of charge carrier and the mobility of the charge carriers are determined from the measurements.

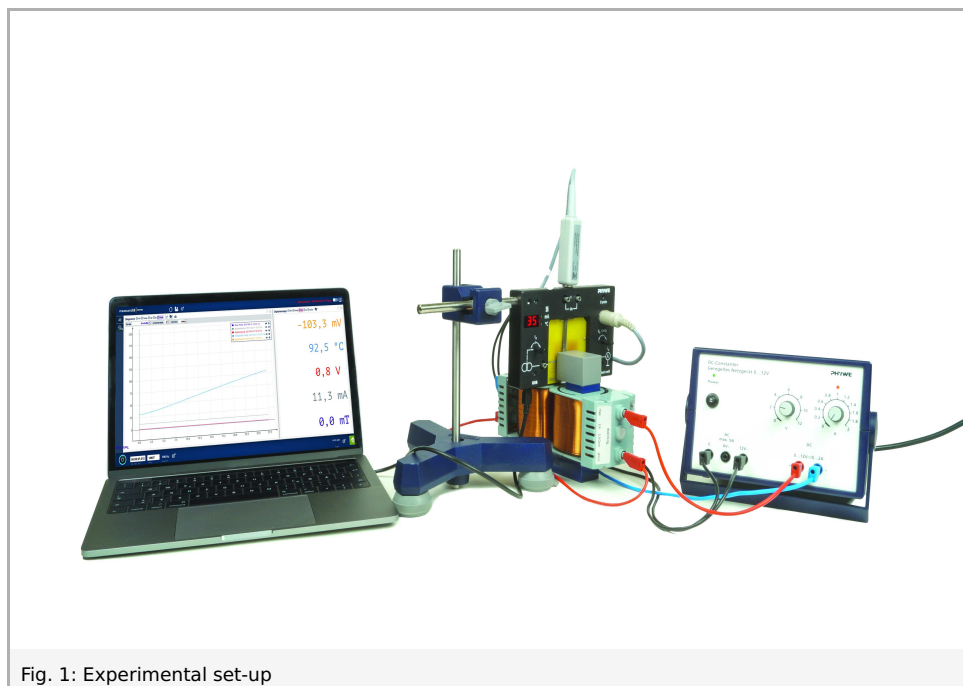


Fig. 1: Experimental set-up

## Equipment

Position No.	Material	Order No.	Quantity
1	PHYWE Hall-effect unit HU 2	11801-01	1
2	Software measureLAB	14580-61	1
3	Hall effect, p-Ge, carrier board	11805-01	1
4	Hall effect, n-Ge, carrier board	11802-01	1
5	Coil, 600 turns	06514-01	2
6	Iron core, U-shaped, laminated electric steel	06501-00	1
7	Pair of pole pieces, plane, 30 x 30 x 48 mm	06489-00	1
8	Hall probe, tangential, protection cap	13610-02	1
9	PHYWE power supply, 230 V, DC: 0...12 V, 2 A / AC: 6 V, 12 V, 5 A	13506-93	1
10	Tripod base PHYWE	02002-55	1
11	Support rod, stainless steel, l = 250 mm, d = 10 mm	02031-00	1
12	Right angle clamp PHYWE	02040-55	1
13	Connecting cord, 32 A, 500 mm, red	07361-01	2
14	Connecting cord, 32 A, 500 mm, blue	07361-04	1
15	Connecting cord, 32 A, 750 mm, black	07362-05	2

## Tasks

The following tasks are performed with n-doped and p-doped specimens.

1. The Hall voltage  $U_H$  is measured at room temperature and constant magnetic field as a function of the control current  $I_p$ .
2. The voltage across the sample  $U_p$  is measured at room temperature and constant control current as a function of the magnetic induction  $B$ .
3. The voltage across the sample  $U_p$  is measured at constant control current as a function of the temperature  $T$ . The band spacing of p- and n-germanium is calculated from the measurements.
4. The Hall voltage  $U_H$  is measured as a function of the magnetic induction  $B$ , at room temperature. The sign of the charge carriers and the Hall constant  $R_H$  together with the Hall mobility  $\mu_H$  and the carrier concentration  $p$  are calculated from the measurements.
5. The Hall voltage  $U_H$  is measured as a function of temperature  $T$  at constant magnetic induction.

## Set-up and procedure

### Set-up

The experimental set-up is shown in Fig.1. The test specimen has to be put into the hall-effect-module via the guide-groove. The module is directly connected with the 12 V  $\sim$  output of the power unit over the ac-input on the backside of the module.

The plate has to be brought up to the magnet very carefully, so as not to damage the crystal in particular, avoid bending the plate. It has to be in the center between the pole pieces.

The USB port on the bottom of the module is used to connect the module to the Laptop with a USB cable.

The different measurements are controlled by the software measureLAB. The magnetic field is measured via a Hall probe, which is connected to the module over the port on the frontside of the module, and can be directly put into the groove on the top of the module as shown in Fig. 2. So, you can be sure, that the magnetic flux is measured directly on the test specimen.

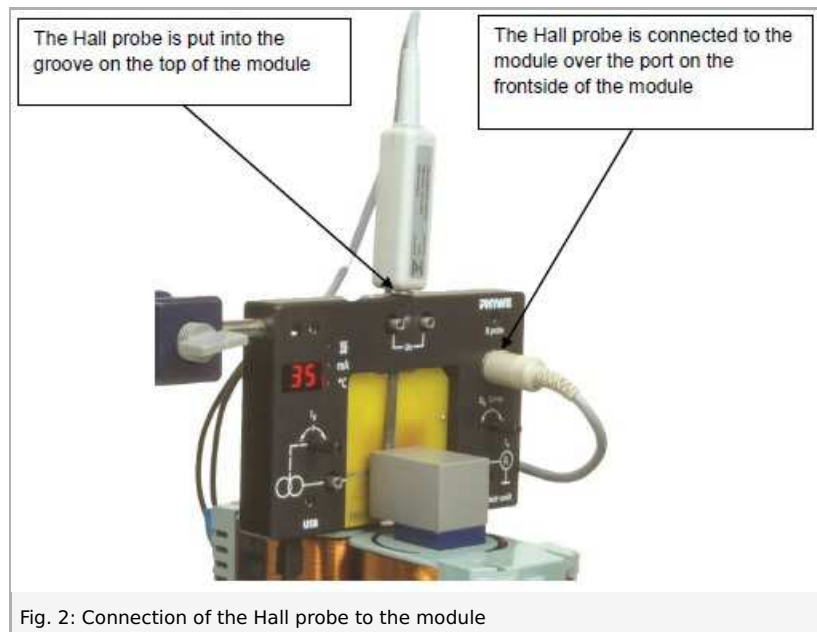


Fig. 2: Connection of the Hall probe to the module

To start the measurements, start the software "measureLAB" and choose the option "Quick start" from the main page (see Fig. 3). You will receive the start-screen, which appears before every measurement (Fig. 4).

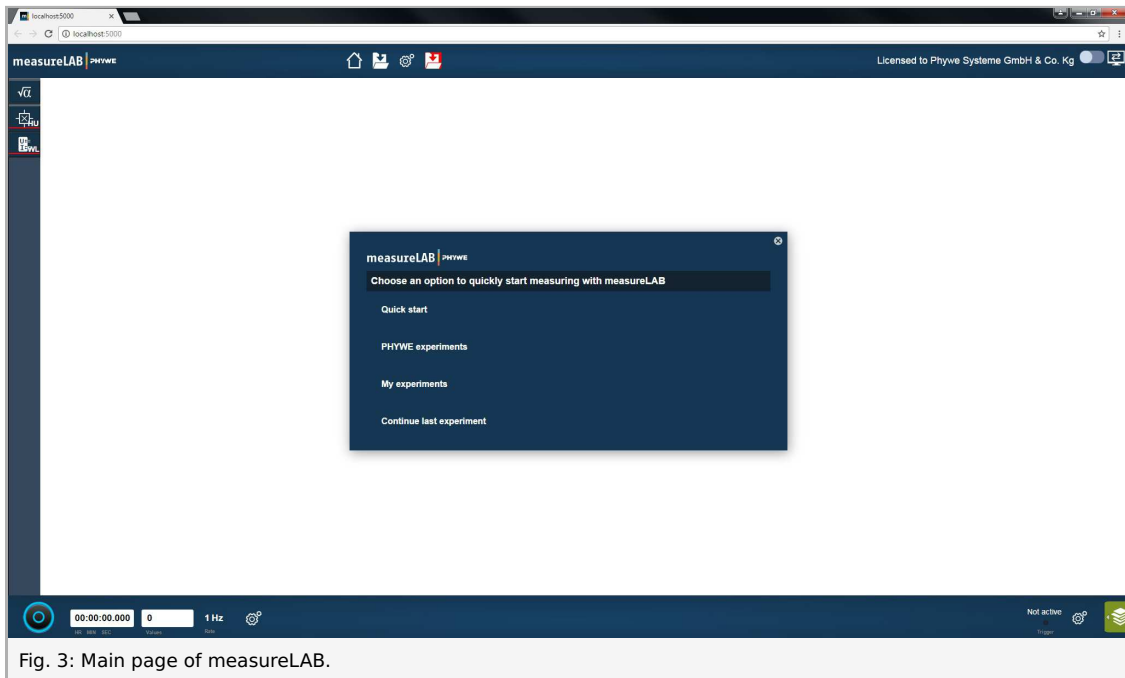


Fig. 3: Main page of measureLAB.

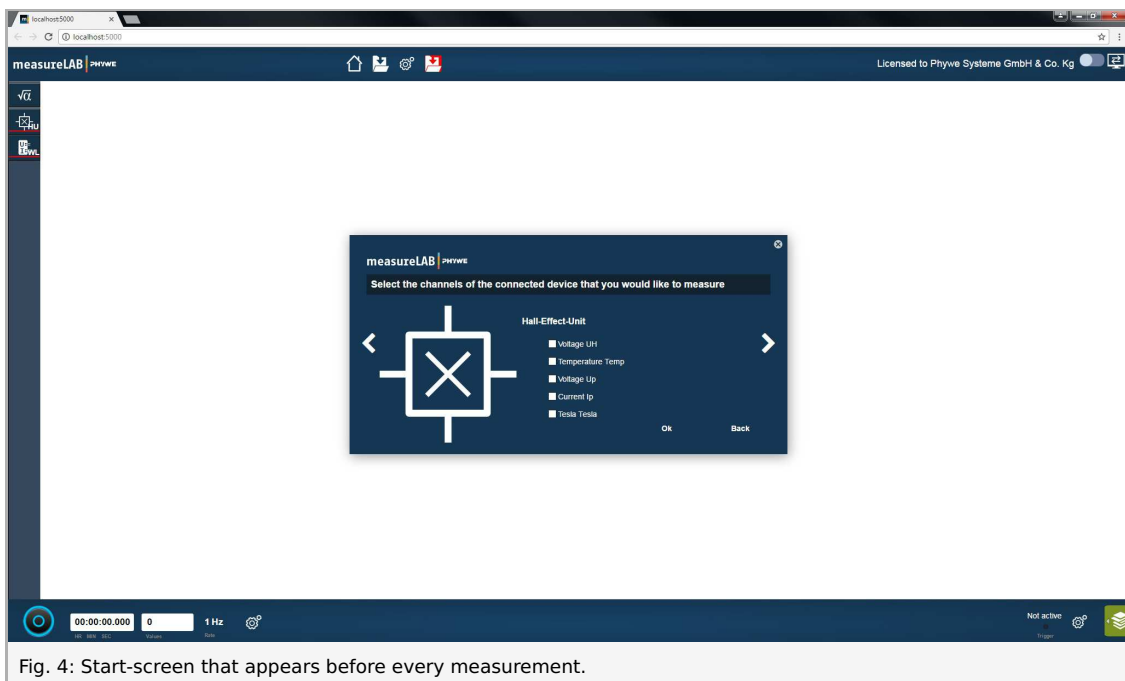


Fig. 4: Start-screen that appears before every measurement.

Here you can choose which parameters have to be measured, displaced, etc. For example, choose the sample voltage  $U_p$  as a function of the temperature  $T$ , and click ok, then you will receive the measurement screen, as shown in Fig. 5. On this screen, you can start the measurement by clicking on the blue bottom in the lower right corner of the screen. The measured values will appear graphically on the "Diagram" and as digital values on the "Digital display".

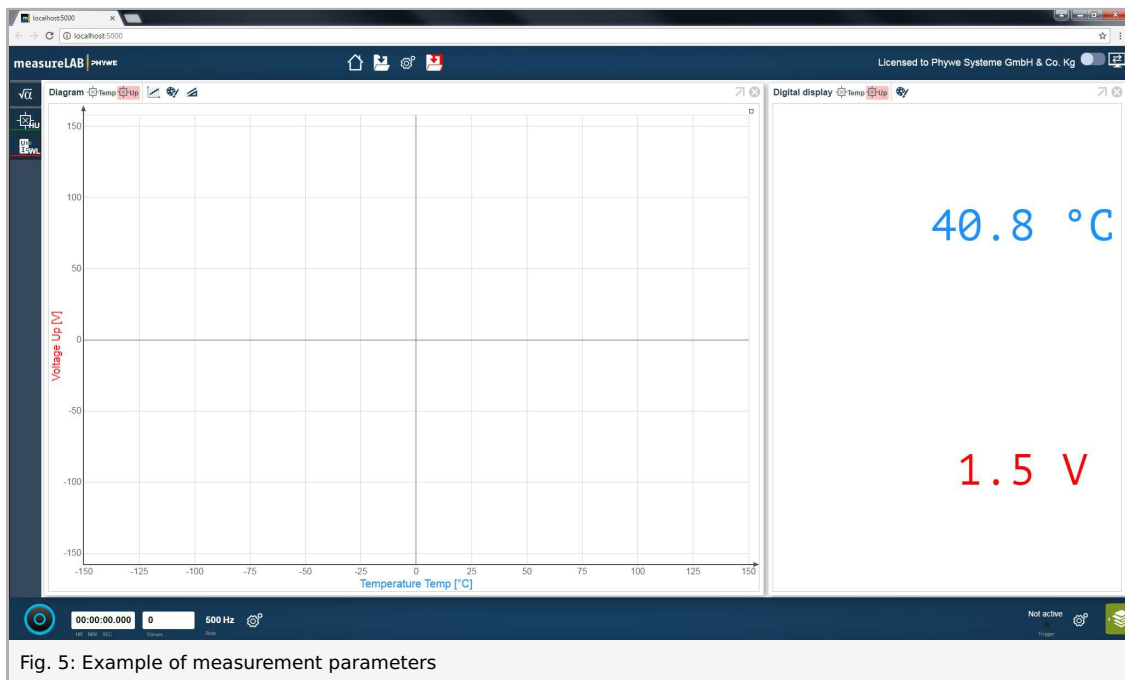


Fig. 5: Example of measurement parameters

## Procedure

### Task 1:

Choose the Hall voltage  $U_H$ , the current  $I_p$  and the magnetic field "Tesla" as measurement parameters from the start screen shown in Fig. 4, and click "Ok". Set the current  $I_p$  and the magnetic field to zero and calibrate the Hall voltage  $U_H$  to zero. Now, set the magnetic field to a value of  $250 \text{ mT}$  by changing the voltage and current on the power supply. Determine the Hall voltage  $U_H$  as a function of the current  $I_p$  from  $-30 \text{ mA}$  to  $30 \text{ mA}$  in steps of  $5 \text{ mA}$ . You will receive a typical measurement like in Fig. 7 (a) and (b) for n- and p-Germanium, respectively.

### Task 2:

Choose the sample voltage  $U_p$ , the current  $I_p$  and the magnetic field "Tesla" as measurement parameters from the start screen shown in Fig. 4, and click "Ok". Set the control current  $I_p$  to  $30 \text{ mA}$ . Determine the sample voltage  $U_p$  as a function of the positive magnetic induction  $B$  up to  $300 \text{ mT}$ . Calculate the change in resistance of the specimens from the measurements and plot the results on graphs as shown in Fig. 8.

### Task 3:

Choose the sample voltage  $U_p$ , the current  $I_p$  and the temperature "Temp" as measurement parameters from the start screen shown in Fig. 4, and click "Ok". At the beginning, set the current  $I_p$  to a value of  $30 \text{ mA}$ . The magnetic field is off. The current  $I_p$  remains nearly constant during the measurement, but the voltage changes  $U_p$  according to a change in temperature  $T$ . Start the measurement by activating the heating coil with the "on/off"-knob on the backside of the module. The specimen will be heated to a maximum temperature of around  $145 - 150 \text{ °C}$  and the module will stop the heating automatically. Determine the cooling curve of the change in voltage  $U_p$  depending on the change in temperature  $T$  for a temperature range from  $140 \text{ °C}$  to room temperature. You will get typical curves as shown in Fig. 9.

### Task 4:

Choose the Hall voltage  $U_H$ , the current  $I_p$  and the magnetic field "Tesla" as measurement parameters from the start screen shown in Fig. 4, and click "Ok". Set the current  $I_p$  and the magnetic field to values of zero and calibrate the Hall voltage  $U_H$  to zero. Now, set the current to a value of  $30 \text{ mA}$ . Determine the Hall voltage  $U_H$  as a function of the magnetic induction  $B$ . Start with  $-300 \text{ mT}$  by changing the polarity of the coil-current on the power supply and increase the magnetic induction in steps of nearly  $20 \text{ mT}$ . At zero point, you have to change the polarity again. A typical measurement is shown in Fig. 10.

### Task 5:

Choose the Hall voltage  $U_H$ , the current  $I_p$ , the temperature "Temp" and the magnetic field "Tesla" as measurement parameters from the start screen shown in Fig. 4, and click "Ok". Set the current  $I_p$  to  $30 \text{ mA}$  and the magnetic induction  $B$  to  $300 \text{ mT}$ . Following the same procedure in task 3 above, determine the Hall voltage  $U_H$  as a function of the temperature  $T$ . You will receive curves like those in Fig. 11.



## Theory and evaluation

### Theory

If a current  $I$  flows through a conducting strip of rectangular section and if the strip is traversed by a magnetic field at right angles to the direction of the current, a voltage – the so-called Hall voltage – is produced between two superposed points on opposite sides of the strip.

This phenomenon arises from the Lorentz force: the charge carriers giving rise to the current flowing through the sample are deflected in the magnetic field  $B$  as a function of their sign and their velocity  $v$ :

$$\vec{F} = e(\vec{v} \times \vec{B})$$

where  $F$  is the force acting on charge carriers and  $e$  is elementary charge.

Since negative and positive charge carriers in semiconductors move in opposite directions, they are deflected also in opposite directions.

The type of charge carrier causing the flow of current can, therefore, be determined from the polarity of the Hall voltage, knowing the direction of the current and that of the magnetic field. That means: if the direction of the current and magnetic field are known, the polarity of the Hall voltage tells us, whether the current is predominantly due to the drift of negative chrgers or to the drift of positive chargers.

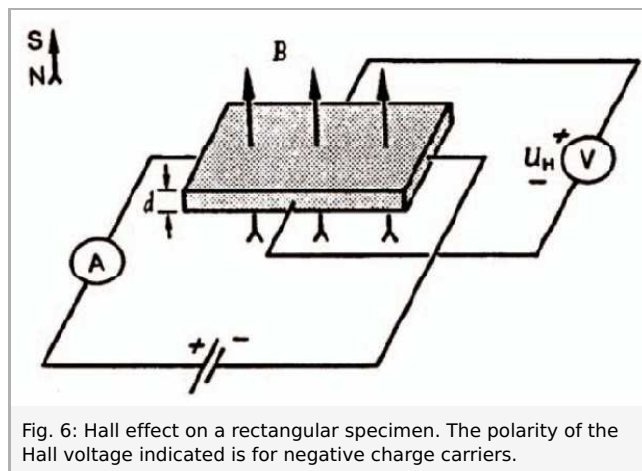


Fig. 6: Hall effect on a rectangular specimen. The polarity of the Hall voltage indicated is for negative charge carriers.

### Evaluation

#### Task 1:

Fig. 7 shows that, for both n-Germanium and p-Germanium, there is a linear relationship between the Hall voltage  $U_H$  and the control current  $I_p$ :

$$U_H = \alpha \cdot I_p$$

where  $\alpha$  is the proportionality factor.

Since the charge carriers in n- and p-Germanium are different, the trend of the linear relationship between  $U_H$  and  $I_p$  is reversed, as shown in Fig. 7 (a) and (b).

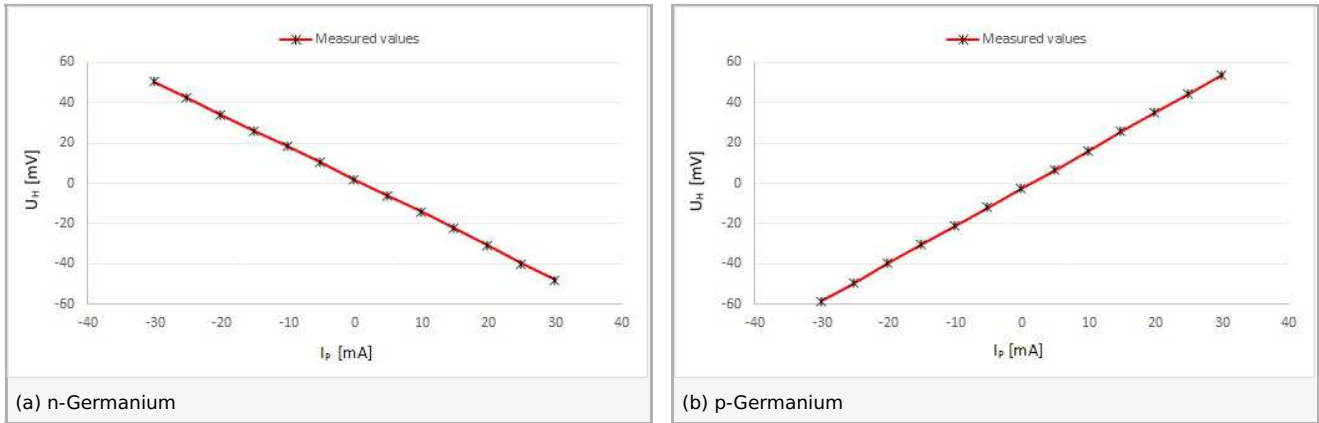


Fig. 7: Hall voltage  $U_H$  as a function of the current  $I_p$  with  $B = 250 \text{ mT}$  and  $T = 300 \text{ K}$ .

**Task 2:**

The change in resistance of the sample due to the magnetic field  $B$  is associated with a reduction in the mean free path of the charge carriers. Since the current  $I_p$  is constant during the measurement, the change of resistance is calculated as

$$\frac{R_m - R_0}{R_0} = \frac{U_m - U_0}{U_0}$$

where  $R_m, U_m$  are resistance and voltage of the sample with the existence of a magnetic field and  $R_0, U_0$  are the resistance and voltage of the sample when the magnetic field  $B = 0$ .

Figs. 8 (a) and (b) show the non-linear change in resistance as the field strength increases for n- and p-Germanium, respectively.

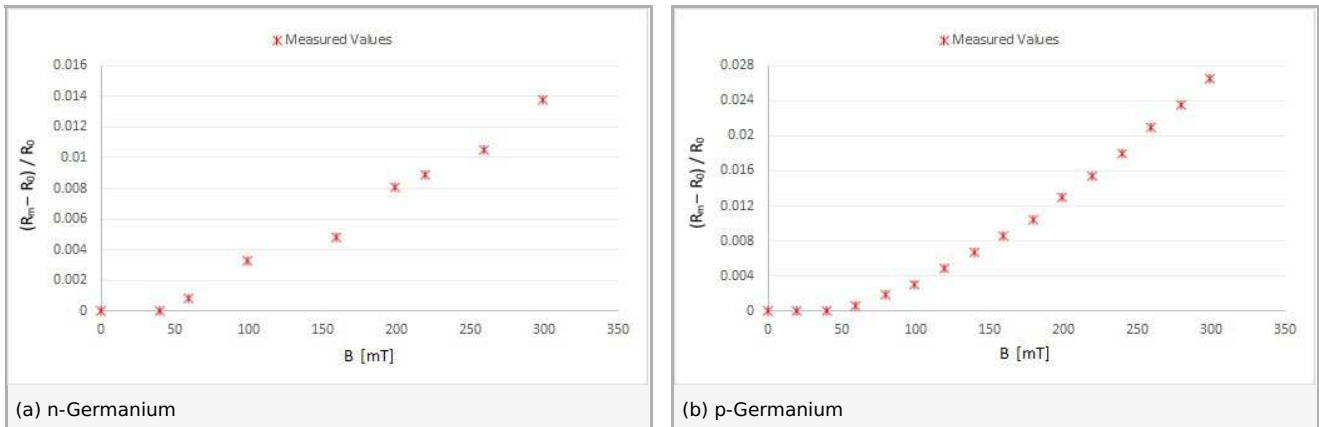


Fig. 8: Change of resistance as a function of the magnetic flux  $B$  with  $I_p = 30 \text{ mA}$  and  $T = 300 \text{ K}$ .

**Task 3:**

In the region of intrinsic conductivity, we have

$$\sigma = \sigma_0 \cdot \exp\left(\frac{E_g}{2kT}\right)$$

where  $\sigma$  = conductivity,  $E_g$  = energy of bandgap,  $k$  = Boltzmann constant,  $T$  = absolute temperature.

By taking the logarithm of both sides of the above equation, we get

$$\ln \sigma = \ln \sigma_0 + \frac{E_g}{2k} \cdot T^{-1}$$

If the logarithm of the conductivity  $\ln \sigma$  is plotted against the reciprocal of the temperature  $T^{-1}$ , a linear relationship is obtained with a slope from which  $E_g$  can be determined. From the measured values shown in Fig. ??, the slopes of the regression lines are

$$b = -\frac{E_g}{2k} = -2.87 \cdot 10^3 \text{ K} \text{ with a standard deviation } s_b = \pm 0.3 \cdot 10^3 \text{ K} \text{ for n-Germanium, and}$$

$$b = -\frac{E_g}{2k} = -4.18 \cdot 10^3 \text{ K with a standard deviation } s_b = \pm 0.07 \cdot 10^3 \text{ K for p-Germanium.}$$



Since  $k = 8.625 \cdot 10^{-5} \frac{\text{eV}}{\text{K}}$ , we get

$$E_g = b \cdot 2k = (0.50 \pm 0.04) \text{ eV} \text{ for n-Germanium, and}$$

$$E_g = b \cdot 2k = (0.72 \pm 0.03) \text{ eV. for p-Germanium.}$$

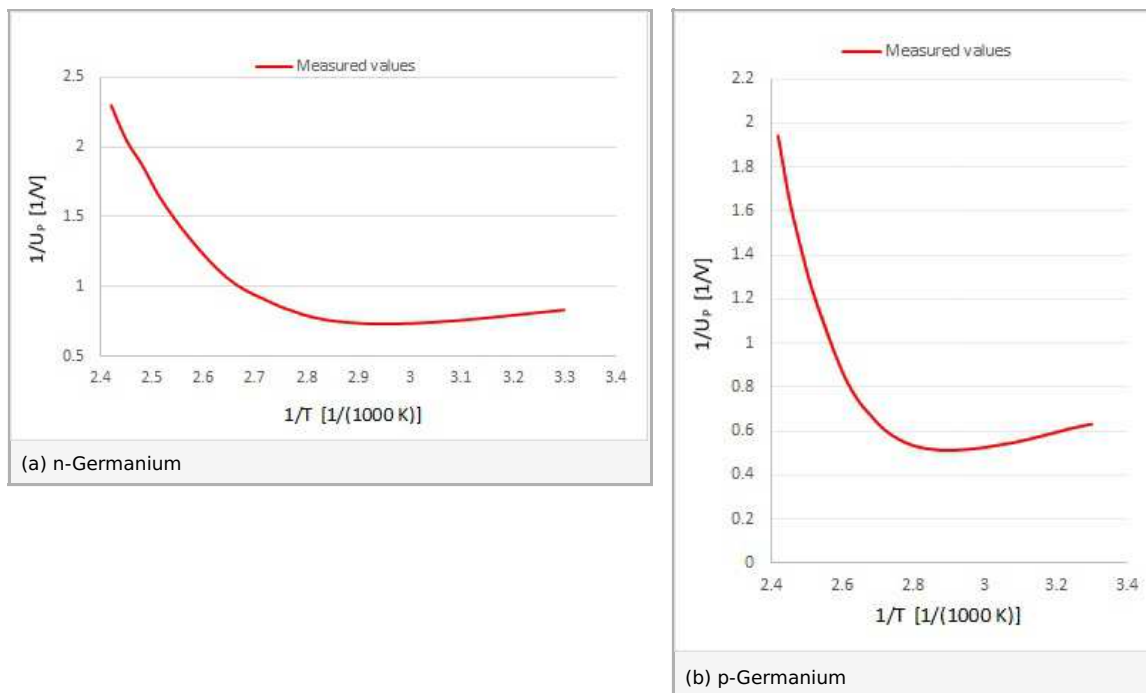


Fig. 9: Reciprocal sample voltage  $1/U_p$  plotted as a function of reciprocal absolute temperature  $1/T$  with  $I_p = 30 \text{ mA}$  and no magnetic flux.

**Task 4**

With the directions of control current and magnetic field shown in Fig. 6, the charge carriers giving rise to the current in the sample are deflected towards the front edge of the sample. Therefore, if (in an n-doped probe) electrons are the predominant charge carriers, the front edge will become negative, and, with hole conduction in a p-doped sample, positive.

The conductivity  $\sigma_0$ , the chargecarrier mobility  $\mu_H$ , and the charge carrier concentration  $p$  are related through the Hall constant  $R_H$ :

$$R_H = \frac{U_H}{B} \cdot \frac{d}{I}$$

$$\mu_H = R_H \cdot \sigma_0$$

$$p = \frac{1}{e} \cdot R_H$$

Fig. 6 shows a linear connection between Hall voltage  $U_H$  and magnetic field  $B$ . With the values used in Fig. 10, the regression line with the formula

$$U_H = U_0 + b \cdot B$$

has a slope  $b = 0.144 \text{ VT}^{-1}$  with a standard deviation  $s_b \pm 0.004 \text{ VT}^{-1}$  for p-Germanium, and  $b = 0.125 \text{ VT}^{-1}$  with a standard deviation  $s_b \pm 0.003 \text{ VT}^{-1}$  for n-Germanium.

The Hall constant  $R_H$  thus becomes, according to

$$R_H = \frac{U_H}{B} \cdot \frac{d}{I} = b \cdot \frac{d}{I}$$

where the sample thickness  $d = 1 \cdot 10^{-3} \text{ m}$  and  $I = 0.030 \text{ A}$ ,

$$R_H = 4.8 \cdot 10^{-3} \frac{\text{m}^3}{\text{As}}$$

with the standard deviation

$$S_{RH} = 0.2 \cdot 10^{-3} \frac{\text{m}^3}{\text{As}} \text{ for n-Germanium, and}$$

$$R_H = 4.17 \cdot 10^{-3} \frac{\text{m}^3}{\text{As}}$$

with the standard deviation

$$S_{RH} = 0.08 \cdot 10^{-3} \frac{\text{m}^3}{\text{As}} \text{ for p-Germanium.}$$

The conductivity at room temperature is calculated from the sample length  $l$ , the sample cross-section  $A$  and the sample resistance  $R$  as follows:

$$\sigma_0 = \frac{l}{R \cdot A}$$

With the measured values

$$l = 0.02 \text{ m}, R = 37.3 \Omega \text{ for n-Ge}, R = 35.5 \Omega \text{ for p-Ge}, A = 1 \cdot 10^{-5} \text{ m}^2$$

we have

$$\sigma_0 = 53.6 \Omega^{-1} \cdot \text{m}^{-1} \text{ for n-Germanium, and}$$

$$\sigma_0 = 57.14 \Omega^{-1} \cdot \text{m}^{-1} \text{ for p-Germanium.}$$

The Hall mobility  $\mu_H$  of the charge carriers can now be determined from

$$\mu_H = R_H \cdot \sigma_0$$

Using the measurements given above, we get

$$\mu_H = 0.257 \pm 0.005 \text{ m}^2/\text{Vs} \text{ for n-Germanium, and}$$

$$\mu_H = 0.238 \pm 0.005 \text{ m}^2/\text{Vs} \text{ for p-Germanium.}$$

The hole concentration  $p$  of p-doped sample is calculated from

$$p = \frac{1}{e} \cdot R_H$$

Using the value of the elementary charge

$$e = 1.602 \cdot 10^{-19} \text{ As}$$

we obtain

$$p = 14.9 \cdot 10^{20} \text{ m}^{-3}.$$

The electron concentration  $n$  of n-doped specimen is given by

$$n = \frac{1}{e \cdot R_H}$$

Taking  $e =$  elementary charge  $= 1.602 \cdot 10^{-19} \text{ As}$ , we obtain

$$n = 13.0 \cdot 10^{20} \text{ m}^{-3}.$$

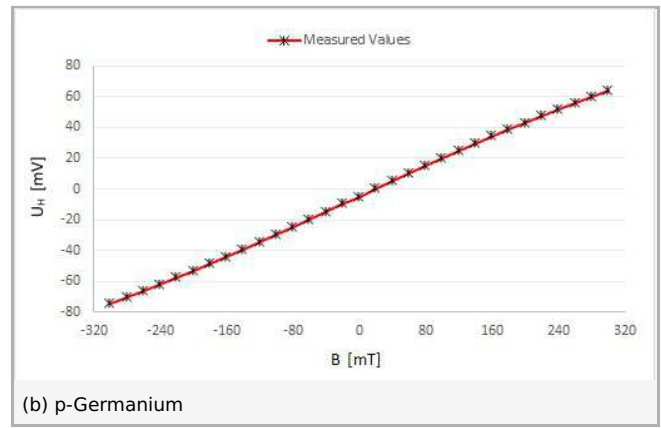
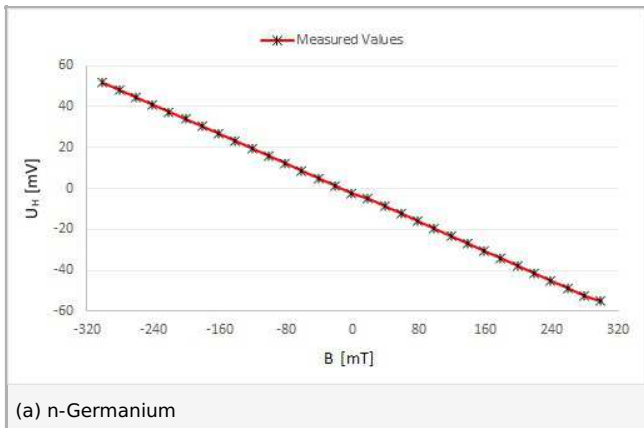


Fig. 10: Hall voltage  $U_H$  as a function of magnetic flux  $B$  with  $I_p = 30 \text{ mA}$  and  $T = 300 \text{ K}$ .

**Task 5:**

Fig. 11 shows that the Hall voltage decreases with increasing temperature for both n- and p-Germanium. Since the experiment was performed with a constant current, it can be assumed that the increase of charge carriers (transition from extrinsic to intrinsic conduction) with the associated reduction of the drift velocity  $v$  is responsible for this. (The same current for a higher number of charge carriers means a lower drift velocity). The drift velocity is in turn related to the Hall voltage by the Lorentz force.

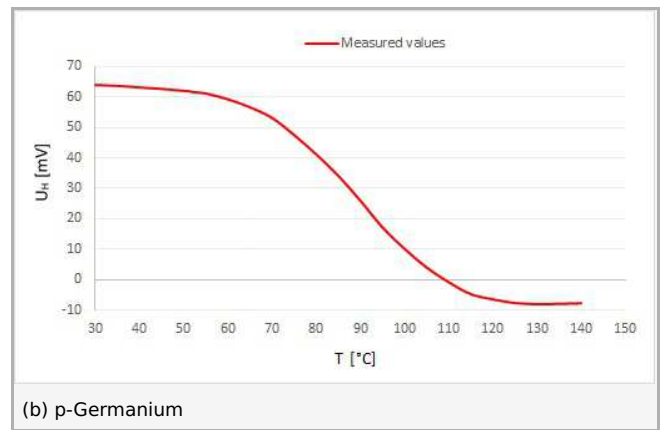
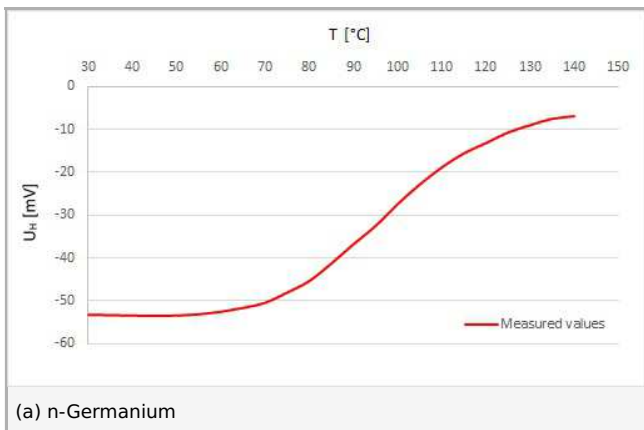


Fig. 11: Hall voltage  $U_H$  as a function of the temperature  $T$  with  $I_p = 30 \text{ mA}$  and  $B = 300 \text{ mT}$ .